

Electronic Patent Application Fee Transmittal

Application Number:	10689506			
Filing Date:	20-Oct-2003			
Title of Invention:	High performance stress-enhanced MOSFETs using Si:C and SiGe epitaxial source/drain and method of manufacture			
First Named Inventor:	Huajie Chen			
Filer:	Andrew Michael Calderon/Liping Qi			
Attorney Docket Number:	FIS920030241US1			
Filed as Large Entity				
Utility Filing Fees				
Description	Fee Code	Quantity	Amount	Sub-Total in USD(\$)
Basic Filing:				
Pages:				
Claims:				
Claims in excess of 20	1202	1	50	50
Independent claims in excess of 3	1201	1	200	200
Miscellaneous-Filing:				
Petition:				
Patent-Appeals-and-Interference:				
Post-Allowance-and-Post-Issuance:				

Description	Fee Code	Quantity	Amount	Sub-Total in USD(\$)
Extension-of-Time:				
Miscellaneous:				
Total in USD (\$)				250